

**Amendment to the Claims:**

This listing of the claims will replace all prior versions, and listings of claims in the present patent application:

**Listing of Claims:**

**Claim 1 (original).** A method for generating an organic plug within a via, said via residing in an integrated circuit structure having a silicon containing dielectric material, said method comprising:

firstly, applying an organic compound to said IC structure, said organic compound configured to occupy said via and a surface of said IC;

secondly, feeding a nitrous oxide (N<sub>2</sub>O) gas into a reactor;

thirdly, generating a plasma in said reactor; and

fourthly, removing a portion of said organic compound so that said organic plug occupies said via.

**Claim 2 (original).** The method of claim 1 wherein said organic compound is an antireflective coating (ARC).

**Claim 3 (original).** The method of claim 1 wherein said organic compound is a bottom antireflective coating (BARC).

**Claim 4 (currently amended).** The method of claim 1 further comprising generating a gas mixture by mixing a diluent with said N<sub>2</sub>O gas ~~said N<sub>2</sub>O gas~~, and applying said gas mixture to said reactor.

**Claim 5 (original).** The method of claim 4 wherein said diluent is a noble gas.

**Claim 6 (original).** The method of claim 1 wherein said method for generating said organic plug is applied during one of a plurality of steps performed during a dual damascene process.

**Claim 7 (original).** The method of claim 1 wherein said silicon containing dielectric material is selected from a group consisting of organosilicate glass (OSG), silicon dioxide ( $\text{SiO}_2$ ), and fluorinated silicate glass (FSG).

**Claim 8 (original).** A method for generating an organic plug within a via, said via residing in an integrated circuit structure having a first photoresist layer, a second intermediate layer, and a third silicon containing dielectric layer, said method comprising:

    firstly, applying an organic compound to said IC structure, said organic compound configured to occupy said via and a surface of said IC;

    secondly, feeding a nitrous oxide ( $\text{N}_2\text{O}$ ) gas into a reactor;

    thirdly, generating a plasma in said reactor; and

    fourthly, removing a portion of said organic compound to generate said organic plug within said via.

**Claim 9 (original).** The method of claim 8 wherein said organic compound is an antireflective coating (ARC).

**Claim 10 (original).** The method of claim 8 wherein said organic compound is a bottom antireflective coating (BARC).

**Claim 11 (currently amended).** The method of claim 8 further comprising generating a gas mixture by mixing a diluent with said N<sub>2</sub>O gas ~~said N<sub>2</sub>O gas~~, and applying said gas mixture to said reactor.

**Claim 12 (original).** The method of claim 11 wherein said diluent is a noble gas.

**Claim 13 (original).** The method of claim 8 wherein said method for generating said organic plug is applied during one of a plurality of steps performed during a dual damascene process.

**Claim 14 (original).** The method of claim 8 wherein said silicon containing dielectric material is selected from a group consisting of organosilicate glass (OSG), silicon dioxide (SiO<sub>2</sub>), and fluorinated silicate glass (FSG).

**Claim 15 (original).** A method for generating an organic plug within a via, said via residing in an integrated circuit structure having a first photoresist layer, a second intermediate layer, and a third silicon containing dielectric layer, said method comprising:

firstly, applying an organic compound to said IC structure wherein said organic compound is a bottom antireflecting coating (BARC), said organic compound configured to occupy said via and a surface of said IC;

secondly, feeding a nitrous oxide ( $\text{N}_2\text{O}$ ) gas into a reactor;

thirdly, generating a plasma in said reactor; and

fourthly, removing a portion of said organic compound to generate said organic plug within said via.

**Claim 16 (currently amended).** The method of claim 16 further comprising generating a gas mixture by mixing a diluent with said  $\text{N}_2\text{O}$  gas ~~said  $\text{N}_2\text{O}$  gas~~, and applying said gas mixture to said reactor.

**Claim 17 (original).** The method of claim 16 wherein said diluent is a noble gas.

**Claim 18 (original).** The method of claim 16 wherein said silicon containing dielectric material is selected from a group consisting of organosilicate glass (OSG), silicon dioxide ( $\text{SiO}_2$ ), and fluorinated silicate glass (FSG).

**Claim 19 (original).** The method of claim 18 wherein said method for generating said organic plug is applied during one of a plurality of steps performed during a dual damascene process.